



电子信息类专业英语

(第2版)

冉利波 主编

教育出版社

DIANZI XINXILEI ZHUANYE YINGYU

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内容简介

本书为《电子信息类专业英语》的第2版。在新版中增加了半导体存储器、自动控制、智能手机、北斗卫星导航系统、LED 液晶电视、物联网、电力电子、智能电网等新的内容。本书分为16课，每课仍分为A段和B段。A段为教学用课文，B段为课后学生阅读材料，所有材料均节选自英文原文资料，其内容具有很强的专业性、实用性和技术先进性，且英文句型简单，难度不高，适合我国高职高专院校学生阅读学习，也可作为应用型本科院校的简明教材和电子信息工程技术人员自学材料。通过本书的学习，不仅可使学生掌握电子信息技术专业词汇和术语，还有利于培养学生阅读电子信息科技文献的能力。每课课文后列出了生词、短语，对难句作了解析，结合课文对科技英语的语法特点、英译汉的技巧作了简单介绍。此外，还介绍了如何撰写科技论文英文摘要和英文求职信。每课课后均附有练习。为培养学生实际翻译能力，在练习中选入了英文说明书、广告等实用文体供学生翻译练习。书后附有课文参考译文及练习参考答案。

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前 言

应高等教育出版社之邀,《电子信息类专业英语》现在再版了。在这一版,编者对原教材作了一些修改。首先,本教材出版已七年了,这七年电子信息技术有了很大的进步。例如,3G、4G 通信的运营,智能手机的出现和普及,物联网的出现,集成电路集成度的进一步提高,等等。因此,从技术角度来说,有必要将这些新的技术加在教材中,以使学生了解有关知识及相关英语词汇、表达方式等。为此,在新版的教材中加入了半导体存储器、自动控制、智能手机、北斗卫星导航系统、LED 液晶电视、物联网、电力电子、智能电网等内容。其中,第 6 课的 Passage A 段换成 Semiconductor Memory,原 Passage A 的 CDs and DVDs 放到 Passage B;第 9 课 Passage B 换成 Automatic Control;考虑到物联网的快速发展,将 15 课的多媒体换成了 Internet of Things。编者注意到有些电子信息类专业的毕业生也在强电方面就业,所以增加了电力电子一课,列为第 16 课,其中 Passage A 为 Power Electronics, Passage B 为 Smart Grid,供授课教师选用。其他内容则补充在原有课文中。其次,因为课文的修改,所以难句解析也做了相应的修改。为使学生掌握科技英语,语法应用加入了更多的科技例句。最后,由于课文内容变动,因而课后练习也做了一些修改。编者希望对本书的这些修改,在专业内容方面和英语内容方面学生都能更喜欢,并更适应当前学生的水平。

学了专业英语就要用。对于在校大学生首先用到的就是毕业论文英文摘要的撰写。现在的大学生几乎人人都有计算机。一些学生就用计算机来将中文摘要翻译成英文摘要。但这样大部分都是错的。希望同学们用专业英语学到的知识来撰写毕业论文英文摘要,这也是一个很好的练习。

本书第 1 版由冉利波、安凤华、胡翠华、穆丽伟编写。第 2 版仍由冉利波主编,但由于工作忙等各种原因,安凤华、胡翠华、穆丽伟三位老师未参加第 2 版的编写,另邀兰英、雷香花两位老师参加第 2 版的编写。兰英修改参考译文,雷香花修改疑难解析。其余的修改由冉利波完成并统稿。

非常感谢成都理工大学工程技术学院和电子信息工程系领导的大力支持,非常感谢高等教育出版社的鼓励和支持,非常感谢电子信息工程系同事们在本书修改过程中与编者非常有益的讨论。

由于水平有限,书中难免有欠妥、不足之处,请读者提出宝贵意见,并将您的宝贵意见发到电子邮箱 ranlb@swip.ac.cn,不胜感谢。

冉利波

2015 年 10 月于四川

目 录

Lesson One Semiconductor Devices 半导体器件	1
Passage A Discrete Components 分立元件	1
Passage B Field Effect Transistor 场效应晶体管	7
Lesson Two Microchip 微芯片	12
Passage A Integrated Circuits 集成电路	12
Passage B Field Programmable Gate Arrays (FPGA) 现场可编程门阵列	16
Lesson Three Power Supplies 电源	20
Passage A Basics of Power Supply 电源基础	20
Passage B Uninterruptible Power Supply (UPS) 不间断电源	25
Lesson Four Radio and Audio 无线电和音频	29
Passage A AM, FM and DAB Broadcasting 调幅、调频、数字无线电广播	29
Passage B MP3	34
Lesson Five Digital Technology 数字技术	38
Passage A Digital Basics 数字技术基础	38
Passage B Digital Camera 数码相机	42
Lesson Six Storage 存储器	46
Passage A Semiconductor Memory 半导体存储器	46
Passage B CDs and DVDs 压缩碟片 (CD) 和数字视频光盘 (DVD)	51
Lesson Seven Television 电视	56
Passage A What are HDTV and DTV 什么是高清电视和数字电视	56
Passage B Plasma TV, LCD TV and LED TV 等离子体电视、液晶电视、发光二极管电视	60
Lesson Eight Measure Instruments 测量仪器	67
Passage A Oscilloscopes 示波器	67
Passage B Multimeters 万用表	72
Lesson Nine Data Acquisition and Processing 数据获取及处理	79
Passage A Data Acquisition System 数据获取系统	79
Passage B Automatic Control 自动控制	84
Lesson Ten Microcontrollers and Their Applications 微控制器及其应用	89
Passage A Microcontrollers 微控制器	89
Passage B Embedded System 嵌入式系统	95
Lesson Eleven PCB 印制电路板	99
Passage A Introduction to PCB Manufacture PCB 制造介绍	99

Passage B	Electrical Grounding 电气接地	104
Lesson Twelve	Computer and Networks 计算机和网络	109
Passage A	Computer and Computer Networks 计算机和计算机网络	109
Passage B	Software 软件	115
Lesson Thirteen	Radio Telecommunications 无线电通信	119
Passage A	Mobile Telecommunications 移动通信	119
Passage B	iPhone	124
Lesson Fourteen	Optical Communications 光通信	128
Passage A	Optical Fibre and its Applications in Communications 光纤及其在通信中的应用	128
Passage B	Global Positioning System (GPS) 全球定位系统	133
Lesson Fifteen	Internet of Things 物联网	138
Passage A	Internet of Things 物联网	138
Passage B	Bluetooth 蓝牙	144
Lesson Sixteen	Power Electronics 电力电子	147
Passage A	Power Electronics 电力电子	147
Passage B	Smart Grid 智能电网	152
参考译文		157
练习参考答案		197
参考文献		210

1

Semiconductor Devices

本课学习重点

- ☞ 掌握有关半导体分立元件，如二极管、晶体管（三极管）、场效应晶体管的基本单词、词组和缩略语的基本含义及用法
- ☞ 培养阅读翻译有关半导体分立元件，特别是二极管、晶体管（三极管）、场效应晶体管的科技文献和产品说明书的能力，主要是英译汉的能力
- ☞ 学习科技英语特点及被动语态在科技英语中的使用，掌握其翻译方法

Passage A Discrete Components

Semiconductor devices are electronic components and manufactured both as single discrete devices, including diodes and transistors, and as integrated circuits (ICs), consisting of a number—from a few (as low as two) to billions—of devices manufactured and interconnected on a single semiconductor substrate, or wafer. Nowadays semiconductor devices have replaced thermionic devices (vacuum tubes) in most applications.

Diodes are the simplest type of semiconductor device with only one PN junction, formed by joining together two pieces of semiconductor, one doped N-type, and the other doped P-type, resulting in a depletion zone to form around the junction (the join) between the two doped materials. This depletion zone controls the behaviours of the diode and permits current to flow predominantly in only one direction. When the P-type region of the P-N junction is connected to the positive terminal of a power supply, the current will flow and this is said to be forward bias. However, when the terminals of a power supply are reversed, there will be a tiny current through the diode and this is called reverse bias.

The current I passing through the diode depends upon the voltage V applied between the two leads and the I - V characteristic curve do not obey Ohm's Law but an exponential relationship of the general form $I = I_0(e^{eV/kT} - 1)$, schematically shown in Figure 1-A1, where I_0 is the leakage current in reverse bias, e is the electron charge, V is bias voltage, k is Boltzmann's constant, T is absolute temperature. When a small voltage V is applied to the diode in the forward direction, there can be a small current to flow the diode and lead to a voltage drop V_{on} of about 0.6 - 1V, which is often referred to as the

diode's "forward voltage drop" and almost 0.7 V in the case of silicon diode. The forward voltage drop V_{on} has to be considered in a circuit as many diodes are used in series, and also, the amount of current passing through the diodes must be considered. When the diode is reverse biased, there will have a very large resistance, but a tiny current, i. e. leakage current, through the diode still exists, from several mA to just μA , normally that can be neglected. The limiting voltages and currents permissible must be considered in practical application. For example, when used for rectification, the diodes have to withstand a reverse voltage. If the diodes are not chosen properly, they will be broken down.

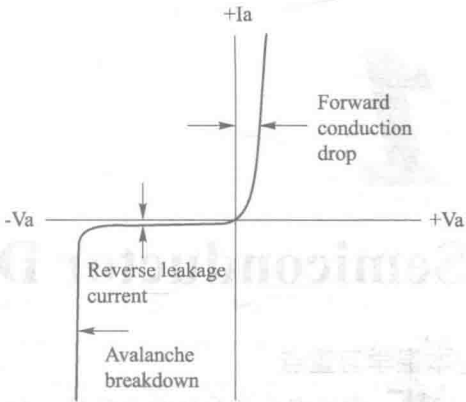


Figure 1-A1 Diode volt-ampere characteristics

There are many different types of semiconductor diodes, such as junction diode which commonly is used in switching applications; Zener diode which is used to regulate voltage by taking advantage of the fact that Zener diodes tend to stabilize at a certain voltage when that voltage is applied in the opposite direction; light emitting diode (LED) which can emit light when current flows through it in the forward direction; photosensitive diode across which the voltage drop depends on the amount of light that strikes it and which can be used to measure illumination, etc..

Transistors are one of the most common types of semiconductor and widely used in electronics and can be broadly grouped into bipolar and field effect types. Silicon tends to be the preferred choice as it has much better characteristics and better thermal stability and repeatability than germanium, although germanium is still used sometimes. A bipolar transistor essentially consists of a pair of PN junction diodes that are joined back-to-back. This forms a sort of a sandwich where one kind of semiconductor, N-type or P-type, is placed in between two others. There are therefore two kinds of bipolar transistor, the NPN and PNP, depending on which type of silicon is used for the "meat" in the sandwich. The bipolar transistor has three terminals, labeled base (B), collector (C) and emitter (E) respectively and the arrow on the component diagram usually shows the emitter terminal, shown in Figure 1-A2. The letters refer to the layers of semiconductor material made the transistor. The direction of the arrow indicates the direction of the current and shows the transistor is NPN or PNP. The principle of operation of the two types of transistor is the same apart from the direction of the current flow through the device.

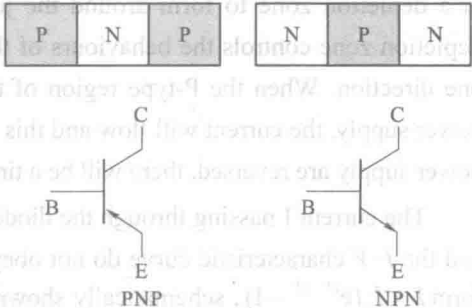


Figure 1-A2 Base, collector and emitter terminal in PNP and NPN bipolar transistor

The bipolar transistor is a current-controlled device, in which a small current applied to the base terminal will control a much larger current to flow from the collector to the emitter terminal with the relationship $I_C = \beta I_B$, where β is current gain, the values of which can be taken in the range 20 to 200 and is not a constant even for a

given transistor. It increases for larger emitter currents because the larger number of electrons injected into the base exceeds the available holes for recombination so the fraction, which recombine to produce base current, declines even further.

A transistor in a circuit can have four working regions, schematically shown in Figure 1-A3, as following:

1) Cut off region (no collector current), useful for “switch off” operation.

2) Active region (some collector current more than a few tenths of a volt above the emitter), useful for amplifier applications.

3) Saturation region (collector a few tenths of a volt above emitter), large current useful for “switch on” applications.

4) Avalanche breakdown region, transistor will be broken down.

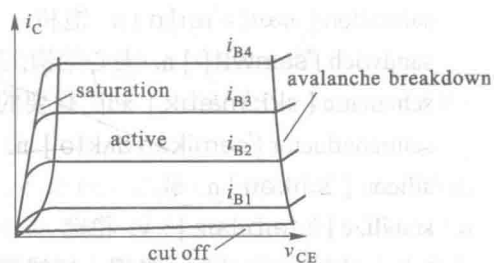


Figure 1-A3 Characteristic curve and working regions of a NPN transistor



Words and Expressions

avalanche ['ævələ:nʃ] n. 雪崩

bipolar [,baɪ'pəʊlə] adj. 有两极的, 双极的

depletion [dɪ'pli:ʃən] n. 耗散

discrete [dɪ'skri:t] adj. 不连续的, 分立的

diode ['daɪəʊd] n. 二极管

doping ['dəʊpɪŋ] n. (半导体) 掺杂 (质)

electronics [ɪ,lek'trɒnɪks] n. 电子学

exponential [,ekspə'nenʃl] adj. 指数的

gain [geɪn] n. 增益, 获得 v. 得到, 增进

germanium [dʒɜ:'meɪniəm] n. 锗

illumination [ɪ ,lu:mi'neɪʃn] n. 照明, 阐释

material [mə'tɪəriəl] n. 材料 adj. 物质的

obey [ə'beɪ] v. 服从, 听从

permissible [pə'mɪsəbl] adj. 可允许的

photosensitive [,fəʊtəʊ'sensətɪv] adj. 光敏的, 感光性的

preferred [prɪ'fəd] adj. 首选的

predominantly [prɪ'dɒmɪnəntli] ad. 优越地, 卓越地, 主要地

resistance [rɪ'zɪstəns] n. 阻力, 电阻, 阻抗

rectification [,rektɪfɪ'keɪʃn] n. 整流

recombination [ri:'kɒmbə'neɪʃən] n. 复合
 repeatability [ri'pi:tə'bɪlɪtɪ] n. 可重复性, 反复性
 saturation [ˌsætʃə'reɪʃən] n. 饱和
 sandwich ['sænwɪtʃ] n. 夹心结构, 三明治 vt. 夹入中间
 schematic [ski:'mæɪtɪk] adj. 扼要的, 图解的
 semiconductor ['semɪkən'dʌktə] n. 半导体
 silicon ['sɪlɪkən] n. 硅
 stabilize ['steɪbalaɪz] v. 稳定
 terminal ['tɜ:mɪnəl] n. 终端, 接线端
 thermal ['θɜ:ml] adj. 热的, 热量的
 transistor [træn'zɪstə] n. 晶体(三极)管
 thyristor [θaɪ'rɪstə] n. 晶闸管
 withstand [wɪð'stænd] v. 抵抗, 对抗
 base terminal 基极
 bipolar transistor 双极型晶体(三极)管
 broken down 击穿
 collector terminal 集电极
 depletion zone 耗尽层
 emitter terminal 发射极
 forward bias 正向偏置
 in series 连续地, 串联
 leakage current 漏电流
 Light Emitting Diode (LED) 发光二极管
 photosensitive diode 光敏二极管
 P-type region P型区
 P-N junction P-N结
 reverse bias 反向偏置
 Silicon Controlled Rectifier (SCR) 晶闸管(可控硅)
 Zener Diode 齐纳二极管(稳压二极管)



Notes to Passage A

1. 难句解析

(1) When a small voltage V is applied to the diode in the forward direction, there can be a small current to flow the diode and lead to a voltage drop V_{on} of about 0.6–1 V, which is often referred to as the diode's "forward voltage drop" and almost 0.7 V in the case of silicon diode. 当一个小的电压 V

正向加到二极管时，就会有一个小的电流流过，会产生一个大约为 0.6~1 V 的电压降 V_{on} ，这常被认为是二极管的“正向电压降”，对于硅二极管而言，此值大约为 0.7 V。

in the case of 意为：就…来说，至于…。例如：

In the case of him, he is qualified for the job. 就他的情况而言，他适合这个工作。

注意 in the case of 与 in case of 意义不同。in case of 意为：假使…，如果发生…，万一…。例如：

In case of fire, ring the alarm bell. 如遇火情，请按警铃。

(2) The limiting voltages and currents permissible must be considered in practical application. For example, when used for rectification, part of the time diodes will be required to withstand a reverse voltage. If the diodes are not chosen properly, they will break down. 在实际应用中，必须考虑二极管的容许电压和容许电流的大小。例如，当用二极管整流时，有时就要求二极管能够承受住反向电压。若二极管选择不当，它们将会被毁坏。

这里 permissible 是形容词用作后置定语，修饰前面的名词 currents，意为“容许电流”。一般来讲，形容词作定语常常放在名词之前，但有时也可后置，如：time enough, something important (修饰不定代词的形容词必须后置)。

(3) Zener diode which is used to regulate voltage, by taking advantage of the fact that Zener diodes tend to stabilize at a certain voltage when that voltage is applied in the opposite direction. 齐纳二极管常利用其加上反向电压时往往趋于稳定在某一电压这一特性来稳压。

• 注意与 use 固定搭配的用法：

be used to do (被用来做…)，例如：

Photosensitive diode across which the voltage drop depends on the amount of light that strikes it and which can be used to measure illumination, etc. 光敏二极管，它的电压降大小依赖于照射在它上面的光照总量的多少，可以用它测量光照强度等。

be used as (被用作…)，例如：

Linear ICs can be used as audio-frequency (AF) and radio-frequency (RF) amplifiers. 线性集成电路可以用于音频和射频放大器中。

be used for (被用于…)，例如：

There are two kinds of bipolar transistor, the NPN and PNP, depending on which type of silicon is used for the “meat” in the sandwich. 根据“夹心层”所用硅类型的不同，有 NPN 和 PNP 两种类型的双极型晶体管。

be used to doing/sth. (习惯于…)，例如：

He is not used to hard manual work. 他不习惯于艰苦的体力劳动。

used to do (过去常常做…)，例如：

He used to smoke heavily. 他过去吸烟很凶。

• that 引导的从句是同位语从句，修饰 fact。

(4) The bipolar transistor is a current-controlled device. 双极型晶体管是由电流控制的器件。current-controlled 意为“由电流控制的”，是由“名词+动词过去分词”构成的复合形容词。例如：snow-covered road 大雪覆盖的马路；computer-controlled traffic lights 计算机控制的交通信号灯；points-based system 计点积分体系。也有由“副词+动词过去分词”构成的复合形容词，

例如: widely-spread rumor 广为传播的谣言; well-prepared speech 准备充分的演讲; well-planned campus 规划有序的校园。

2. 语法应用

(1) 科技英语的特点

科技英语是用专业语言描述客观存在的事物或事实的英语。科技英语与一般英语并没有本质的区别,因而,在语法规则上与一般英语相同。但科技英语与用于文学、政论、商务、新闻等方面的英语有所不同,有其特殊性,其特点可简单归纳为如下几点:

① 大量使用科技专业词汇、复合词和缩略词。

② 科技文章是以文字叙述为主,辅以数学公式、图形、表格等,因此科技英语文体主要使用陈述句和祈使句。在学术论文、科普文章、专著、教科书、技术总结报告、实验报告、技术函件、专利申请书及投标申请等文献中主要使用陈述句;而在用户手册、操作规程、技术说明书中,除使用陈述句外,还常使用祈使句。时态常用一般现在时及一般过去时,少用现在完成时及过去完成时。

③ 科技文章叙述内容要求客观、真实,因而,要求用词准确、逻辑性强、句式严整,且大量使用被动语态、名词化结构、It...that...句型、非谓语动词、形容词短语作后置定语、介词加动名词短语、分词及不定式短语、分词独立结构等。在分析和解释所观察到的各种现象时,有时要提出各种各样的假设,因而经常使用虚拟语气。纵观科技文献我们可以看到科技英语复杂长句多、被动语态多、非谓语动词多。

上述这些特点将分别在以后各课中介绍,本课则重点介绍被动语态在科技英语中应用的特点、语法规则及翻译特点:

(2) 被动语态在科技英语中应用的特点

在科技文章里广泛使用被动语态,常常将主要信息或科学技术事实作为主语放在句首,而动作的执行者则由 by 引导,放在后面,且常常省略。这是由于科技英语主要是叙述科学技术事实,以客观陈述为主,强调动作的承受者,不强调动作的执行者。特别要注意的是在科技文献中动作的执行者常常是人,如人类、科技工作者自己等。如过多使用以 I, we, you 等词为主语的主动语态,会造成主观臆断的印象。因此,要尽量避免使用以 I, we, you 等人称代词为主语的主动态,而用被动态,且略去 I, we, you 等词。本文中的很多句子都是被动态。例如:

The diode is the simplest type of semiconductor device with only one PN junction, which is formed by joining together two pieces of semiconductor, one doped N-type, and the other doped P-type. 二极管是最简单的、仅有一个 PN 结的半导体器件,此 PN 结由两块半导体结合在一起而被形成,两片半导体中的一片被掺杂成 N 型,而另一片被掺杂成 P 型。

其中的定语从句 which is formed by joining together two pieces of semiconductor 就是被动态。这里 which 代表 PN junction,是动作的承受者,动名词短语 joining together two pieces of semiconductor 是动作的执行者,由 by 来引导,也可以理解为方法或手段。

(3) 科技英语中被动语态翻译的特点

① 科技英语中由 by 引导的被动语态的动作执行者,译成汉语时,by 可译为“被”、“由...”、“给”、“使”等。例如:

When the battery terminals are reversed, the P-N junction almost completely blocks the current flow and this is called reverse bias. 当电源方向被反接时,PN 结几乎完全阻塞了电流的流动,这

种电源方向反接的情况被称为“反向偏置”。其中 the battery terminals are reversed 和 this is called reverse bias 都是被动态。动作的承受者分别是 the battery terminals 和 this。

② 在某些情况下,科技英语的被动语态可译成汉语的主动语态,尤其是当被动语态的动作执行者并未明确给出时。例如:

If the diodes are not chosen properly, they will be broken down. 其中 diodes 是动作的承受者,动作的执行者虽未给出,但可以看出动作执行者是人,故翻译时可加上主语,“你”或“我们”,译成主动态,即“若你选择二极管不当,它们将被击穿”。

③ 科技英语中常用 It is said that (“据说”), It is reported that (“据报道”), It is supposed that (“据推测”), It must be pointed out that (“必须指出”)等特殊被动语态句型,这些被动语态句型可以翻译成无主语的汉语句子。例如:

It must be pointed out that if the diodes are not chosen properly, they will be broken down. 必须指出,若二极管选择不当,它们将被击穿。

Passage B Field Effect Transistors

Field Effect Transistor (FET) is one type of transistor, which can be used for weak-signal amplification and for analog or digital signal amplification (for example, for amplifying wireless signals), or switch DC or function as an oscillator.

In the FET, current moves in a channel, from the source, labeled S, to the drain, labeled D. A gate terminal, labeled G, generates an electric field that controls the current. The conductivity of the FET depends on the electrical diameter of the channel. A small change in gate voltage can cause a large variation in the current from the source to the drain. This is how the FET amplifies signals.

Field-Effect Transistors are classified as two major classifications, junction FET (JFET) and metal-oxide-semiconductor FET (MOSFET).

The junction FET has a channel consisting of N-type semiconductor (N-channel) or P-type semiconductor (P-channel) material; the gate is made up of the opposite semiconductor type. The symbols of n type and P-type junction FET are shown in Figure 1-B1. In N-channel devices, electrons flow so the drain potential must be higher than that of the source ($V_{DS} > 0$). In P-channel devices, the flow of holes requires that $V_{DS} < 0$. However, under some conditions there is a small current through the junction during part of the input signal cycle. There is very little resistance in the absence of an electric field (no bias voltage). The drain-source resistance is between a few hundred ohms to less than an ohm. The output impedance of devices made with FETs is generally quite low.

In the MOSFET, the channel can be either N-type or P-type semiconductor. The gate electrode is a piece of metal whose surface is oxidized and the oxide layer (such as silicon dioxide, SiO_2)

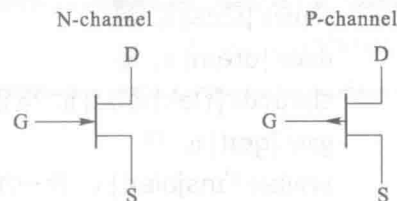


Figure 1-B1 Circuit symbol of N-channel and P-channel JFET

electrically insulates the gate from the channel. For this reason, the MOSFET was originally called the insulated-gate FET (IGFET), but this term is now rarely used. Because the oxide layer acts as a dielectric, there is essentially never any current between the gate and the channel during any part of the signal cycle. This gives the MOSFET has extremely large input impedance, usually greater than 10^{12} ohms (a million megohms). Because the oxide layer is extremely thin, the MOSFET is susceptible to destruction by electrostatic charges. Since MOSFETs can both deplete the channel, like the JFET, and enhance it, every N-type or P-type MOSFET can be enhancement mode or depletion mode. A depletion mode, device (also called a normally on MOSFET) has a channel in resting state that gets smaller as a reverse bias is applied; this device conducts current with no bias applied. An enhancement mode device (also called a normally off MOSFET) is built without a channel and does not conduct current when $V_{GS} = 0$; increasing forward bias forms a channel that conducts current.

The FET has some advantages and some disadvantages relative to the bipolar transistor. Field Effect Transistors are preferred for weak-signal work, for example in wireless communications and broadcast receivers. They are also preferred in circuits and systems requiring high impedance. The FET is not, in general, used for high-power amplification, such as is required in large wireless communications and broadcast transmitters.



Words and Expressions

channel ['tʃænl] n. 道沟

classification [ˌklæsɪfɪ'keɪʃən] n. 分类, 分级

conductivity [ˌkɒndʌk'tɪvətɪ] n. 传导性, 传导率

diameter [daɪ'æmɪtə] n. 直径

dielectric [daɪ'lektrɪk] n. 电介质, 绝缘材料 adj. 介电的, 非传导性的

destruction [dɪ'strʌkʃn] n. 破坏, 毁灭

source [sɔ:s] n. 源

drain [dreɪn] n. 漏

electrode [ɪ'lektroʊd] n. 电极

gate [geɪt] n. 栅

insulate ['ɪnsjʊleɪt] v. 使...绝缘

impedance [ɪm'pi:dnəs] n. 阻抗

oxidize ['ɒksɪdaɪz] v. 氧化, 生锈

susceptible [sə'septəbl] adj. 易受影响的, 容许

FET 场效应管

insulated-gate FET 绝缘栅场效应管

junction FET 结型场效应管



Practices

1. Translate the following English phrases into Chinese:

- 1) semiconductor device
- 2) behaviour of the diode
- 3) exponential relationship
- 4) conventional rectifier
- 5) base terminal
- 6) field effect transistor
- 7) collector current
- 8) direction of the arrow

2. Translate the following Chinese phrases into English:

- 1) 电源的正极
- 2) 一定数量的阻抗
- 3) 电压降
- 4) 几毫安到甚至几微安的漏电流
- 5) 容许电压和容许电流
- 6) 电流控制器件
- 7) 集电极到发射极电流
- 8) 较好的热稳定性和重复性

3. Translate the following product specification into Chinese:

Philips Semiconductors

Product Specifications

High-speed diodes

1N914; 1N914A; 1N914B

Features

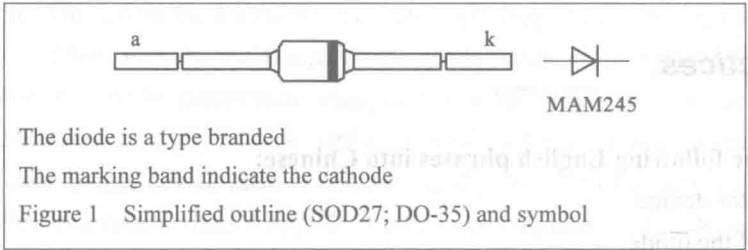
- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed max 4 ns
- Continuous reverse voltage max 75 V
- Repetitive peak reverse voltage max 100 V
- Repetitive peak forward current max 225 mA

Applications

- High speed switching

Descriptions

The 1N914, 1N914A and 1N914B are high speed switching diodes fabricated in planar technology, and encapsulated in a hermetically sealed leaded glass SOD27 (DO-35) package



Limiting Values

in accordance with the Absolute Maximum Rating System (IEC 60134)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage			100	V
V_R	continuous reverse voltage			75	V
I_F	continuous forward current	see note 1		75	mA
I_{FRM}	repetitive peak forward current			225	mA
I_{FSM}	non-repetitive peak forward current	Square wave; $T_j=25\text{ }^{\circ}\text{C}$ prior to surge $t=1\text{ }\mu\text{s}$ $t=1\text{ ms}$ $t=1\text{ s}$		4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb}=25\text{ }^{\circ}\text{C}$; note 1		250	mW
T_{stg}	storage temperature		-65	+200	$^{\circ}\text{C}$
T_j	junction temperature			175	$^{\circ}\text{C}$

Note 1: Device mounted on an FR4 printed-circuit-board; lead length 10 mm.

Electrical characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_f	forward voltage	$I_F=10$ $I_F=5$ $I_F=100\text{ mA}$	— 0.62 —	1 0.72 1	V
I_R	Reverse current	$V_R=20\text{ V}$ $V_R=75\text{ V}$ $V_R=20\text{ V}$; $T_j=150\text{ }^{\circ}\text{C}$	— — —	25 5 50	nA μA μA
C_d	diode capacitance	$f=1\text{ MHz}$; $V_R=0$	—	4	pF
t_{rr}	reverse recovery time	When switch from $I_F=10\text{ mA}$ to $I_R=10\text{ mA}$; $R_L=10\text{ }\Omega$; measured at $I_R=1\text{ mA}$	—	8	ns
V_{fr}	forward recovery time	When switch from $I_F=50\text{ mA}$; $t_f=20\text{ ns}$		2.5	V

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{th\ j-tp}$	Thermal resistance from junction to tie-point	Lead length 10 mm	24	Ω
$R_{th\ j-a}$	Thermal resistance from junction to ambient	Lead length 10 mm; note 2	500	Ω

Note 2: Device mounted on an a printed-circuit-board without metallization pad.

注：本产品说明书节选于 Philips Semiconductors Product Specifications.